CREE

C3M0160120D

Silicon Carbide Power MOSFET
C3M™ MOSFET Technology

N-Channel Enhancement Mode

V_{DS}	1200 V
$I_{D\ @\ 25^{\circ}C}$	17 A
$R_{DS(on)}$	160 mΩ

Features

- C3M™ SiC MOSFET technology
- High blocking voltage with low On-resistance
- High speed switching with low capacitances
- Fast intrinsic diode with low reverse recovery (Qrr)
- Halogen free, RoHS compliant

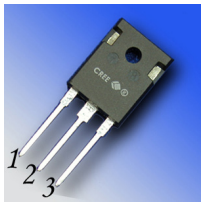
Benefits

- Higher system efficiency
- Reduced cooling requirements
- Increased power density
- Increased system switching frequency

Applications

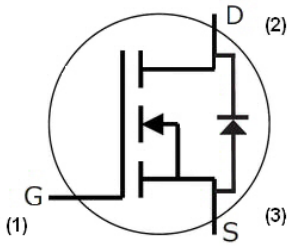
- Renewable energy
- High voltage DC/DC converters
- Switch Mode Power Supplies
- UPS

Package



Halogen-Free

RoHS



Part Number	Package	Marking
C3M0160120D	TO-247-3	C3M0160120D

Maximum Ratings (T_C = 25 ˚C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain - Source Voltage	1200	V	V_{GS} = 0 V, I_D = 100 µA	
V_{GSmax}	Gate - Source Voltage (dynamic)	-8/+19	V	AC (f >1 Hz)	Note: 1
V_{GSop}	Gate - Source Voltage (static)	-4/+15	V	Static	Note: 2
I_D	Continuous Drain Current	17	A	V_{GS} = 15 V, T_C = 25˚C	Fig. 19
		12		V_{GS} = 15 V, T_C = 100˚C	
$I_{D(pulse)}$	Pulsed Drain Current	34	A	Pulse width t_P limited by T_{jmax}	Fig. 22
P_D	Power Dissipation	97	W	T_C=25˚C, T_J = 150 ˚C	Fig. 20
T_J , T_{stg}	Operating Junction and Storage Temperature	-55 to +150	˚C		
T_L	Solder Temperature	260	˚C	1.6mm (0.063”) from case for 10s	
M_d	Mounting Torque	1 8.8	Nm lbf-in	M3 or 6-32 screw	

Note (1): When using MOSFET Body Diode V_{GSmax} = -4V/+19V
Note (2): MOSFET can also safely operate at 0/+15 V

Electrical Characteristics (T_C = 25˚C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1200			V	V_{GS} = 0 V, I_D = 100 µA	
$V_{GS(th)}$	Gate Threshold Voltage	1.8	2.8	3.6	V	V_{DS} = V_{GS}, I_D = 2.33 mA	Fig. 11
			2.2		V	V_{DS} = V_{GS}, I_D = 2.33 mA, T_J = 150ºC	
I_{DSS}	Zero Gate Voltage Drain Current		1	50	µA	V_{DS} = 1200 V, V_{GS} = 0 V	
I_{GSS}	Gate-Source Leakage Current		10	250	nA	V_{GS} = 15 V, V_{DS} = 0 V	
$R_{DS(on)}$	Drain-Source On-State Resistance		160	208	mΩ	V_{GS} = 15 V, I_D = 8.5 A	Fig. 4, 5, 6
			256			V_{GS} = 15 V, I_D = 8.5 A, T_J = 150ºC	
g_{fs}	Transconductance		5.2		S	V_{DS}= 20 V, I_{DS}= 8.5 A	Fig. 7
			4.9			V_{DS}= 20 V, I_{DS}= 8.5 A, T_J = 150ºC	
C_{iss}	Input Capacitance		632		pF	V_{GS} = 0 V, V_{DS} = 1000 V f = 1 MHz V_{AC} = 25 mV	Fig. 17, 18
C_{oss}	Output Capacitance		39				
C_{rss}	Reverse Transfer Capacitance		3				
E_{oss}	C_{oss} Stored Energy		22.5		µJ		Fig. 16
E_{ON}	Turn-On Switching Energy (SiC Diode FWD)		183		µJ	V_{DS} = 800 V, V_{GS} = -4 V/15 V, I_D = 8.5 A, $R_{G(ext)}$ = 2.5 Ω, L= 336 µH, T_J = 150ºC	Fig. 26, 29
E_{OFF}	Turn Off Switching Energy (SiC Diode FWD)		16				
E_{ON}	Turn-On Switching Energy (Body Diode FWD)		294		µJ	V_{DS} = 800 V, V_{GS} = -4 V/15 V, I_D = 8.5 A, $R_{G(ext)}$ = 2.5 Ω, L= 336 µH, T_J = 150ºC	Fig. 26, 29
E_{OFF}	Turn Off Switching Energy (Body Diode FWD)		14				
$t_{d(on)}$	Turn-On Delay Time		30		ns	V_{DD} = 800 V, V_{GS} = -4 V/15 V I_D = 8.5 A, $R_{G(ext)}$ = 2.5 Ω, Timing relative to V_{DS} Inductive load	Fig. 27, 28
t_r	Rise Time		16				
$t_{d(off)}$	Turn-Off Delay Time		20				
t_f	Fall Time		13				
$R_{G(int)}$	Internal Gate Resistance		8		Ω	f = 1 MHz, V_{AC} = 25 mV	
Q_{gs}	Gate to Source Charge		9		nC	V_{DS} = 800 V, V_{GS} = -4 V/15 V I_D = 8.5 A Per IEC60747-8-4 pg 21	Fig. 12
Q_{gd}	Gate to Drain Charge		12				
Q_g	Total Gate Charge		38				

Reverse Diode Characteristics (T_C = 25˚C unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	4.5		V	V_{GS} = -4 V, I_{SD} = 3 A	Fig. 8, 9, 10
		4.0		V	V_{GS} = -4 V, I_{SD} = 3 A, T_J = 150 °C	
I_S	Continuous Diode Forward Current		17	A	V_{GS} = -4 V, T_J = 25 ˚C	Note 1
$I_{S, pulse}$	Diode pulse Current		34	A	V_{GS} = -4 V, pulse width t_P limited by T_{jmax}	Note 1
t_{rr}	Reverse Recover time	34		ns	V_{GS} = -4 V, I_{SD} = 8.5 A, V_R = 800 V dif/dt = 844 A/µs, T_J = 150 °C	Note 1
Q_{rr}	Reverse Recovery Charge	194		nC		
I_{rrm}	Peak Reverse Recovery Current	8		A		

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1.29	°C/W		Fig. 21

Typical Performance

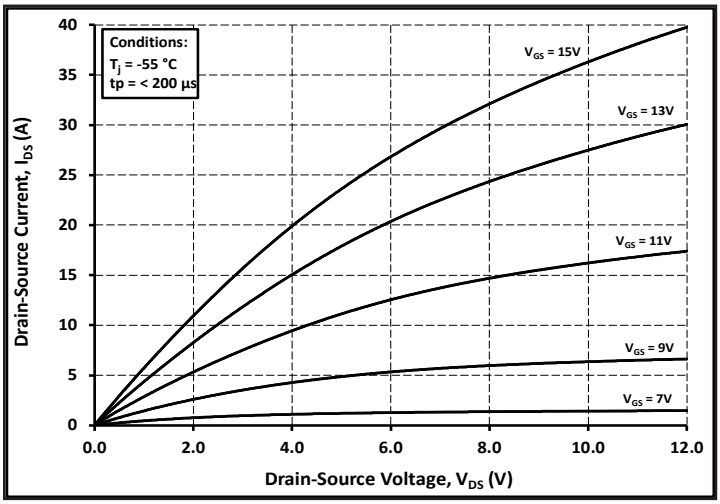


Figure 1. Output Characteristics T_J = -55 ºC

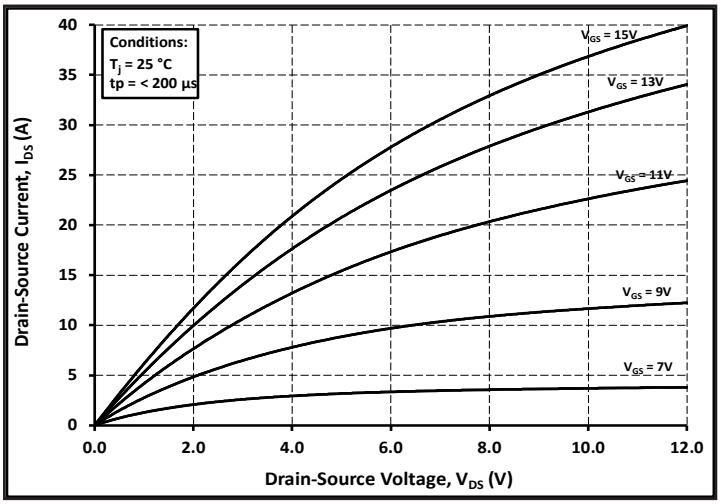


Figure 2. Output Characteristics T_J = 25 ºC

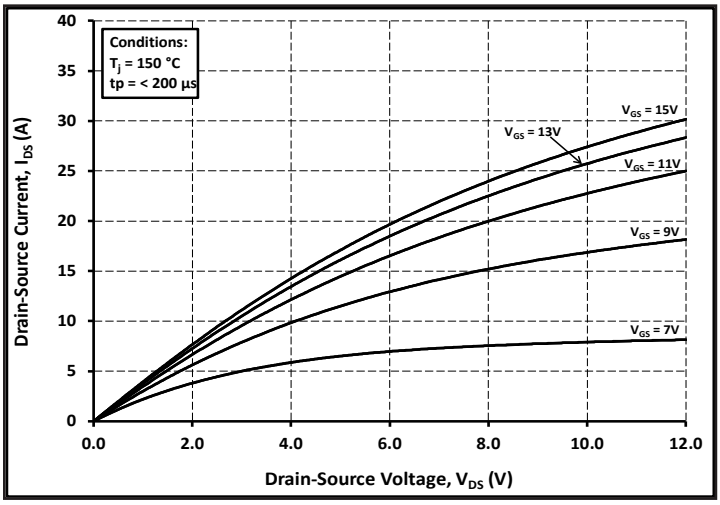


Figure 3. Output Characteristics T_J = 150 ºC

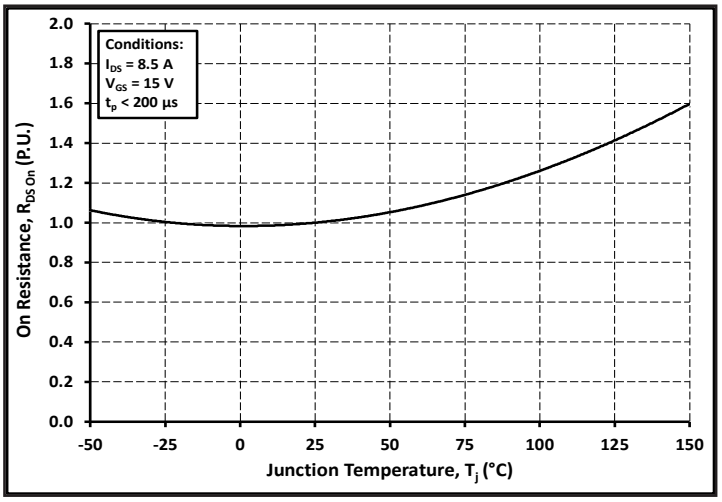


Figure 4. Normalized On-Resistance vs. Temperature

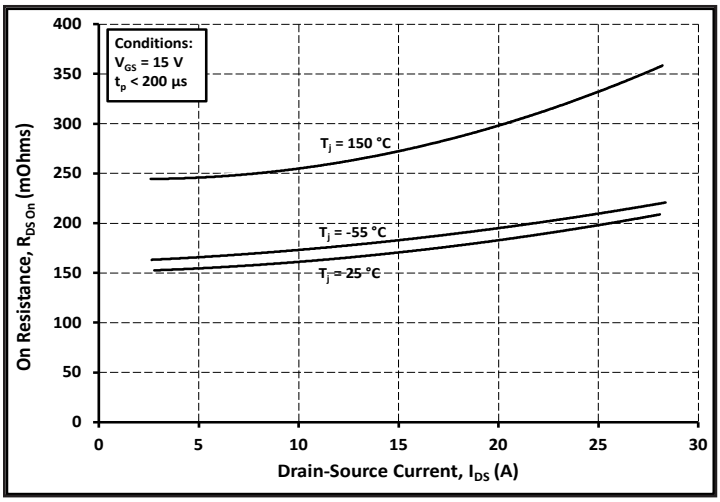


Figure 5. On-Resistance vs. Drain Current
For Various Temperatures

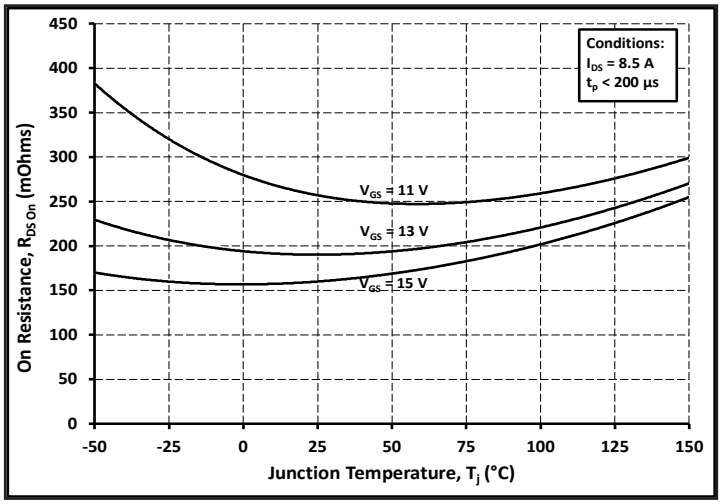


Figure 6. On-Resistance vs. Temperature
For Various Gate Voltage

Typical Performance

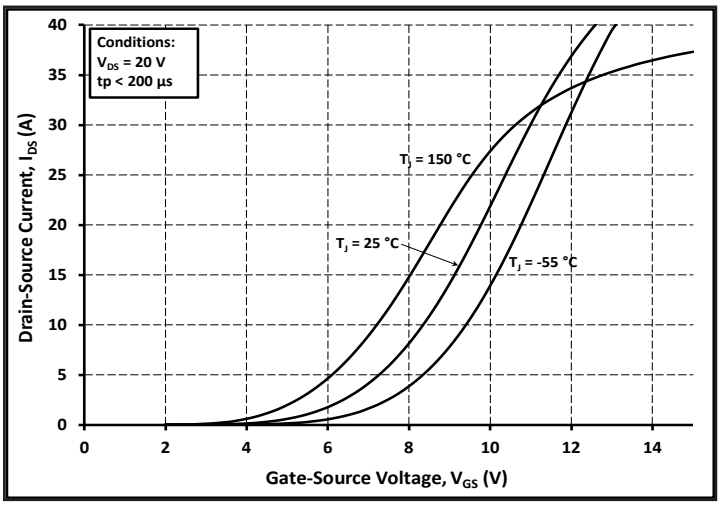


Figure 7. Transfer Characteristic for Various Junction Temperatures

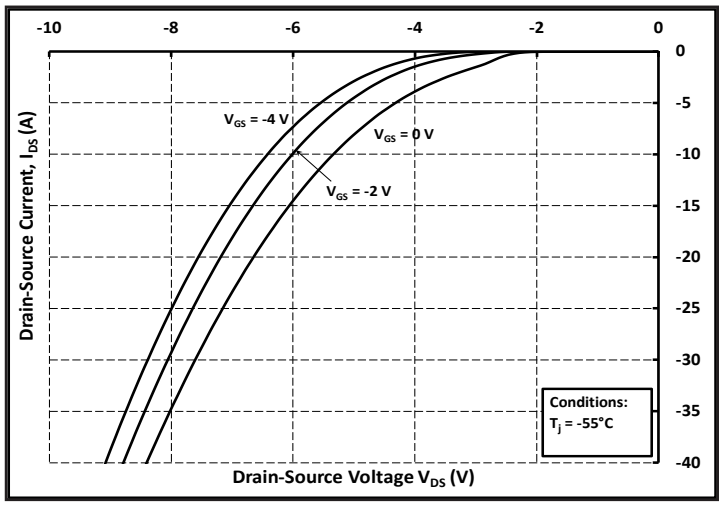


Figure 8. Body Diode Characteristic at -55 ºC

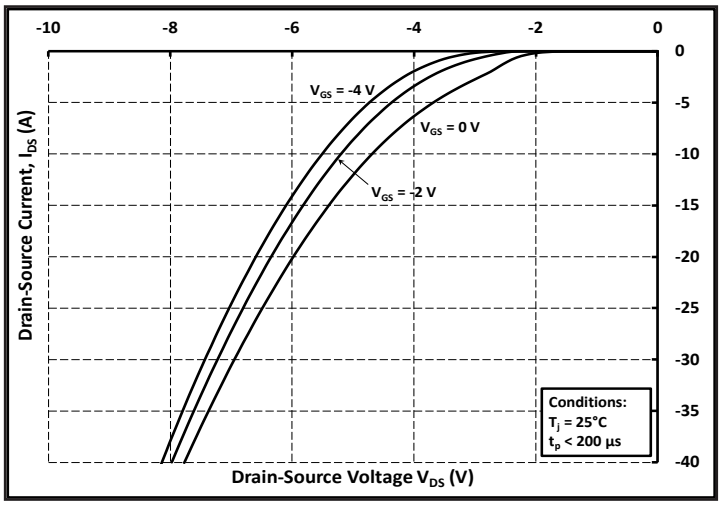


Figure 9. Body Diode Characteristic at 25 ºC

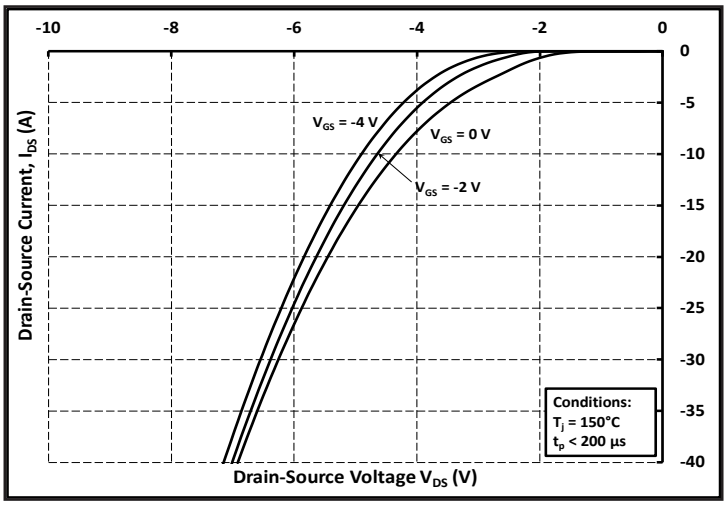


Figure 10. Body Diode Characteristic at 150 ºC

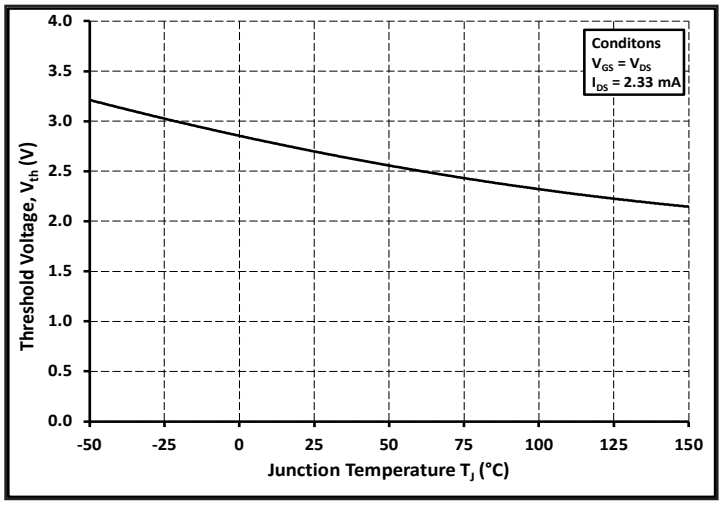


Figure 11. Threshold Voltage vs. Temperature

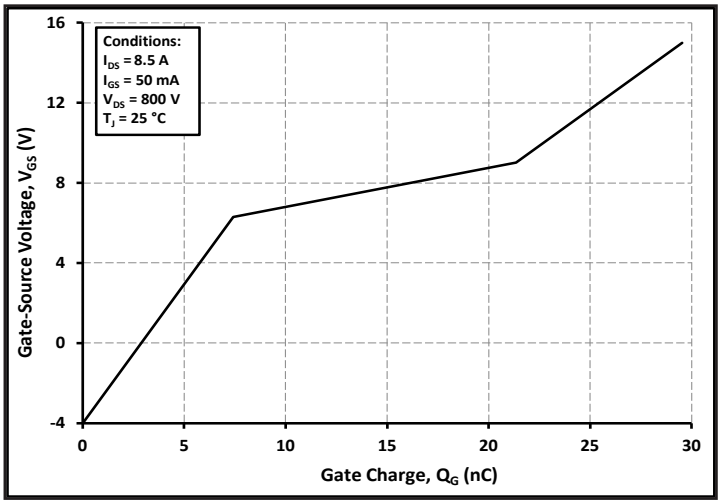


Figure 12. Gate Charge Characteristics

Typical Performance

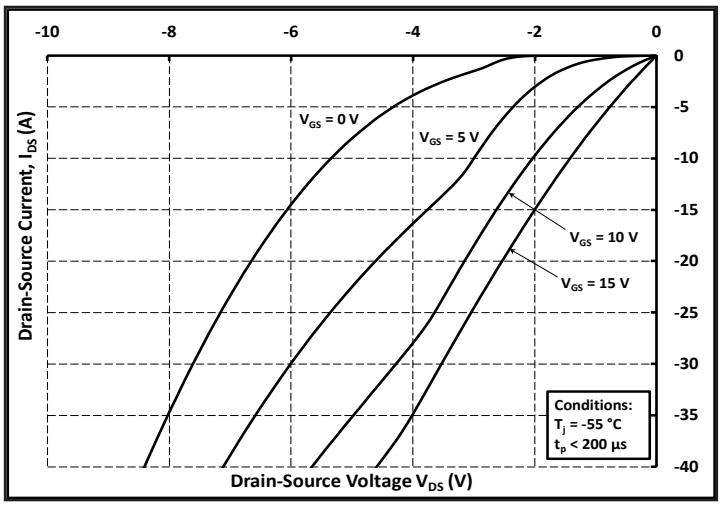


Figure 13. 3rd Quadrant Characteristic at -55 ºC

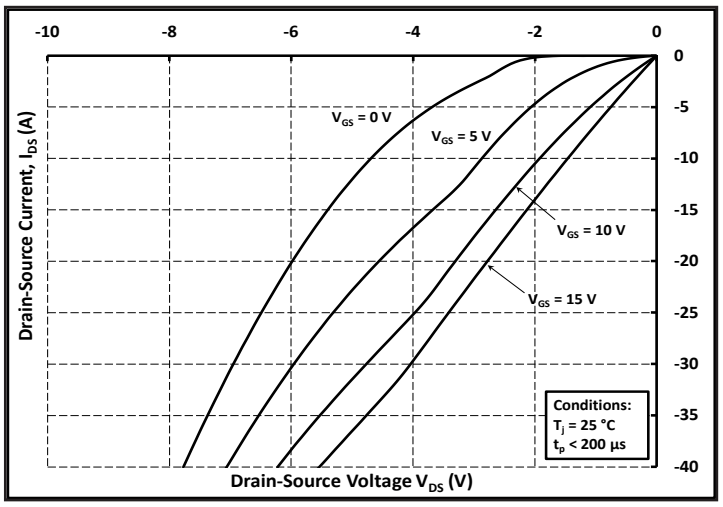


Figure 14. 3rd Quadrant Characteristic at 25 ºC

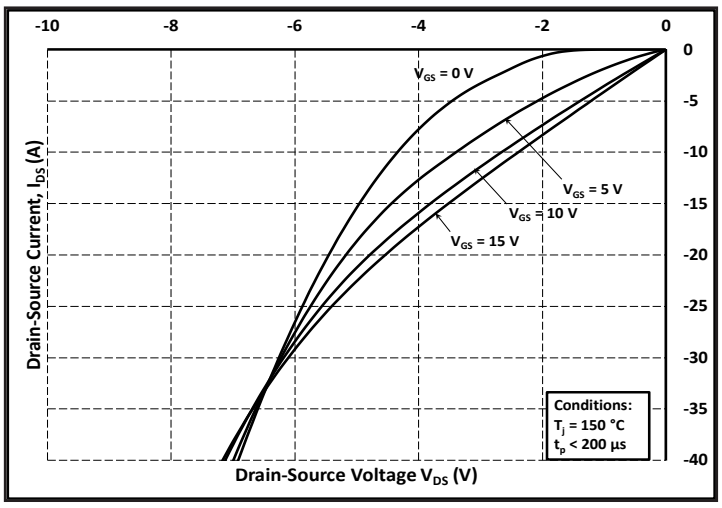


Figure 15. 3rd Quadrant Characteristic at 150 ºC

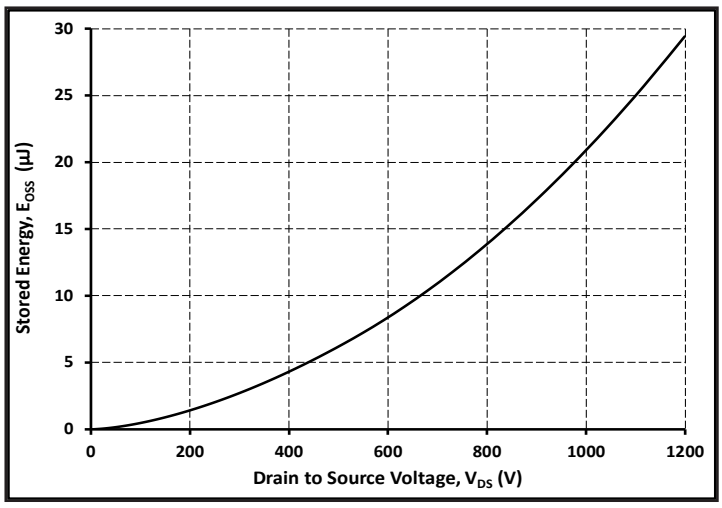


Figure 16. Output Capacitor Stored Energy

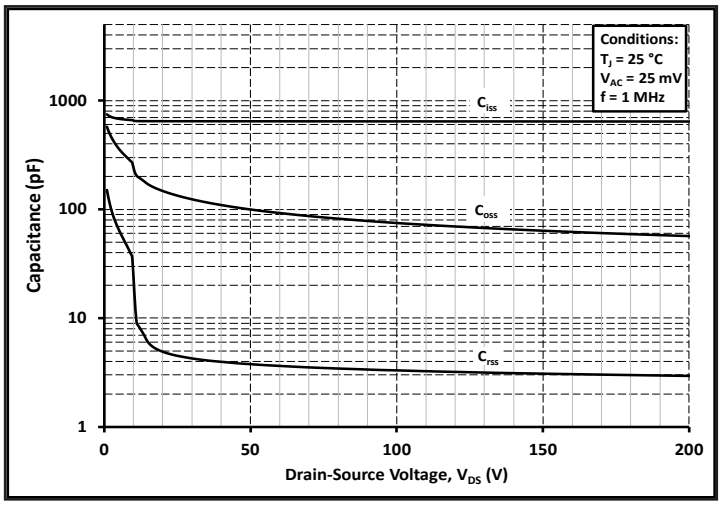


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

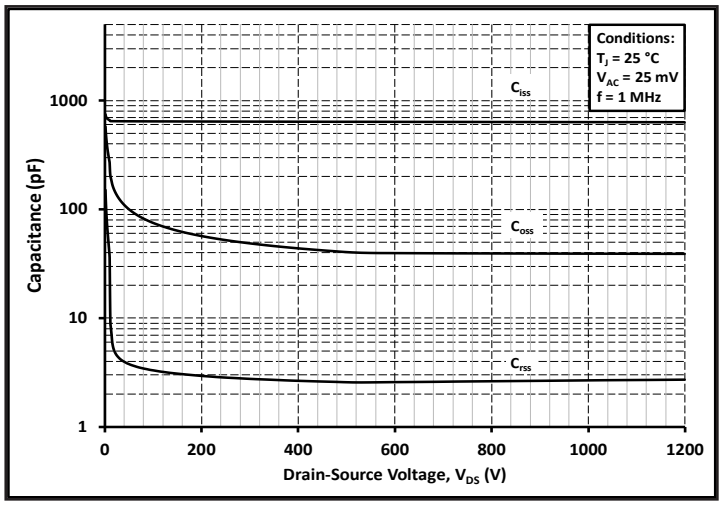


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 1200V)

Typical Performance

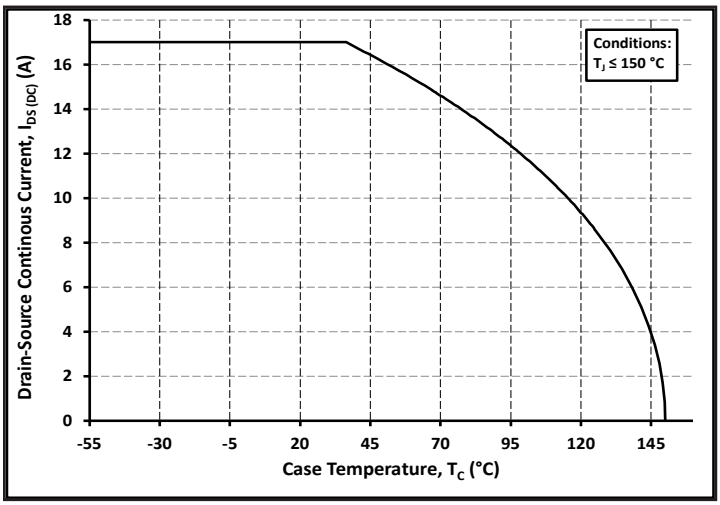


Figure 19. Continuous Drain Current Derating vs. Case Temperature

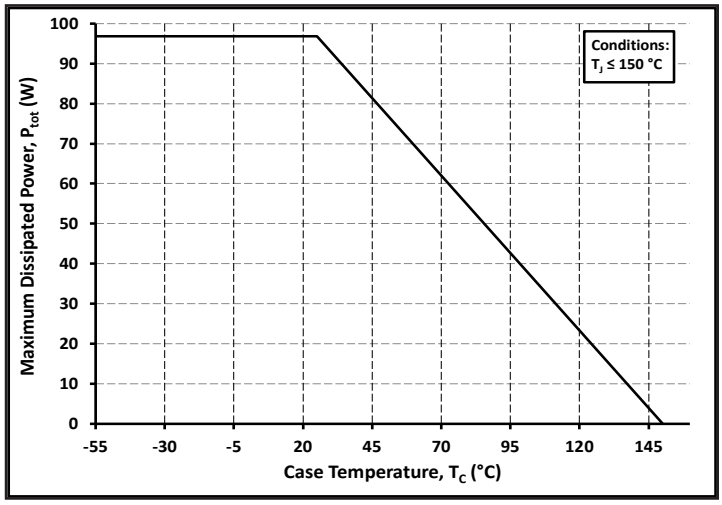


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

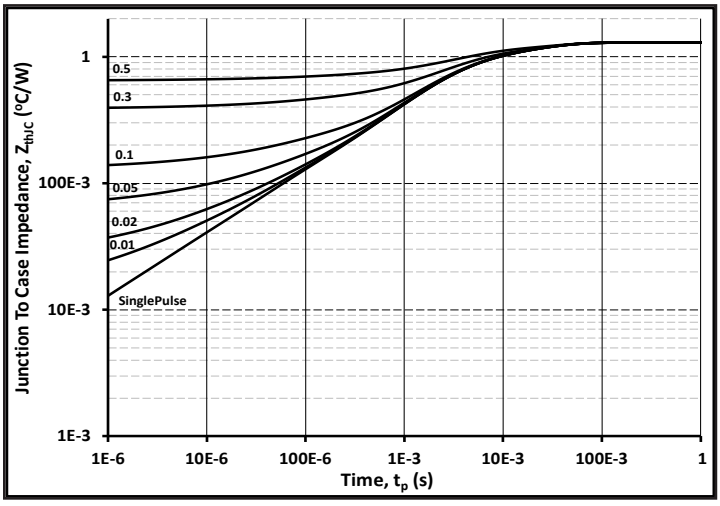


Figure 21. Transient Thermal Impedance (Junction - Case)

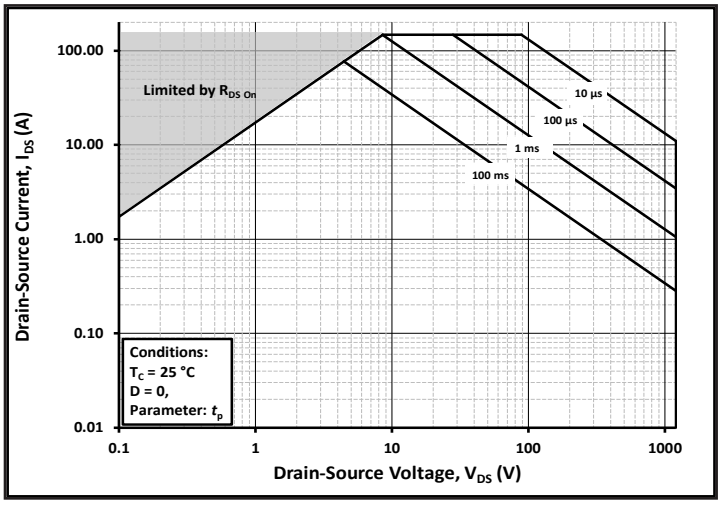


Figure 22. Safe Operating Area

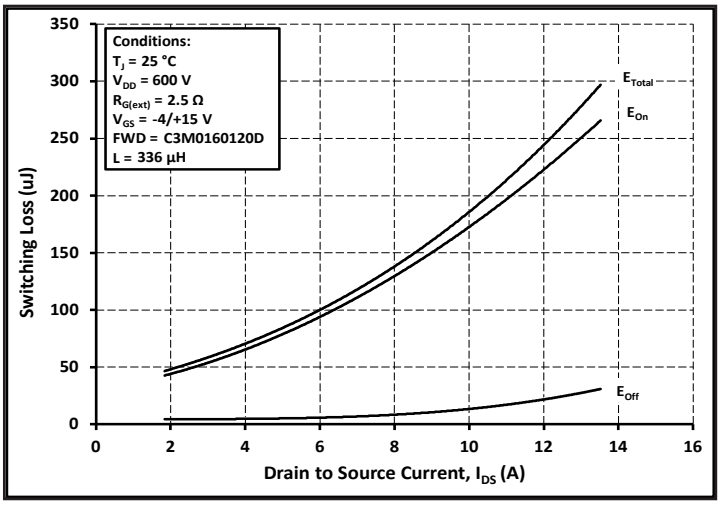


Figure 23. Clamped Inductive Switching Energy vs. Drain Current (V_{DD} = 600V)

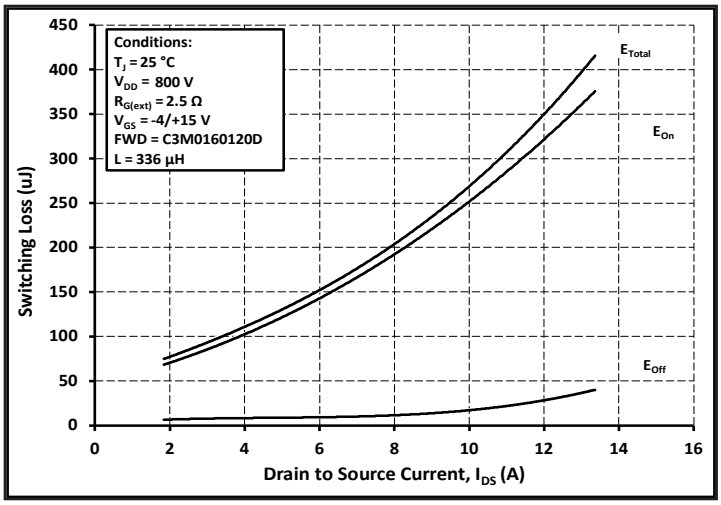


Figure 24. Clamped Inductive Switching Energy vs. Drain Current (V_{DD} = 800V)

Typical Performance

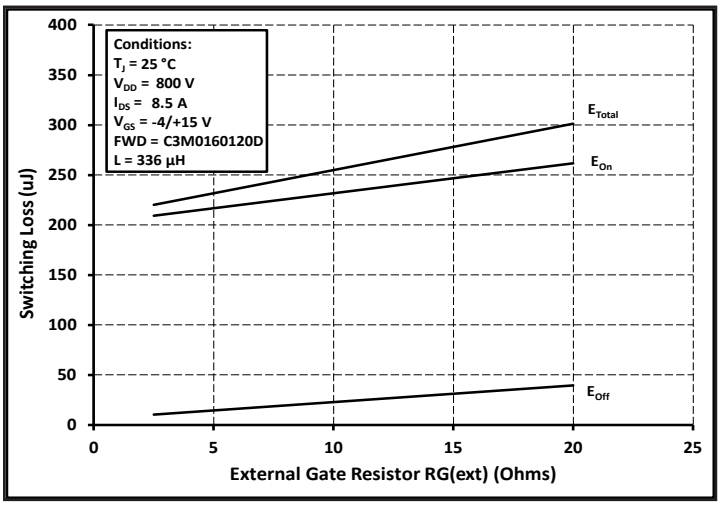


Figure 25. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

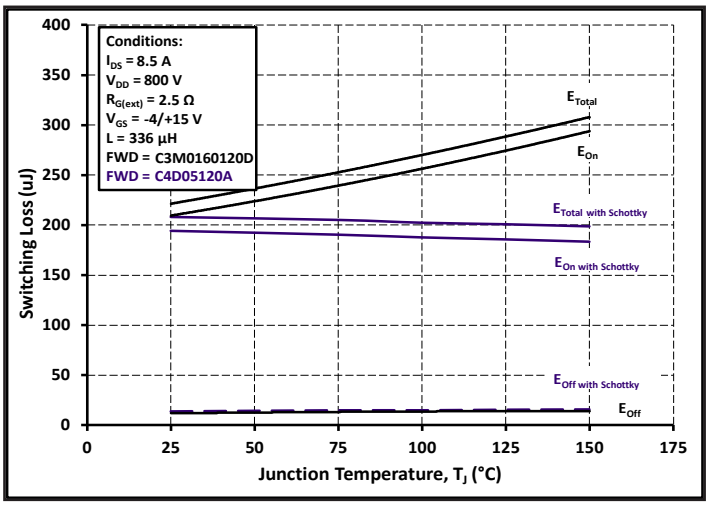


Figure 26. Clamped Inductive Switching Energy vs. Temperature

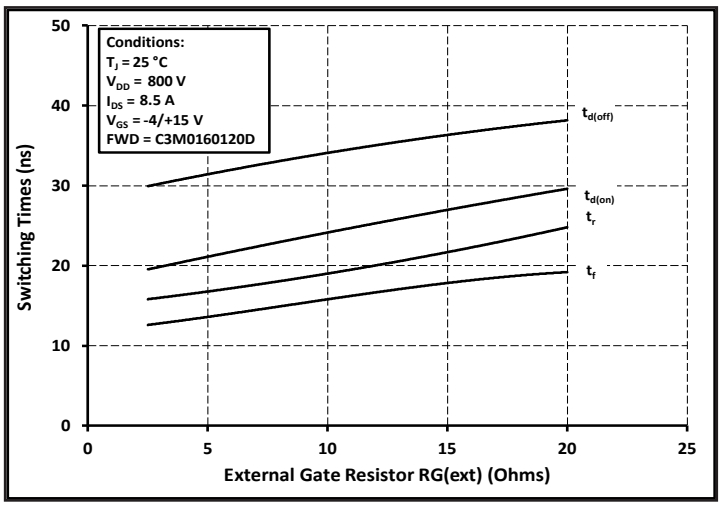


Figure 27. Switching Times vs. $R_{G(ext)}$

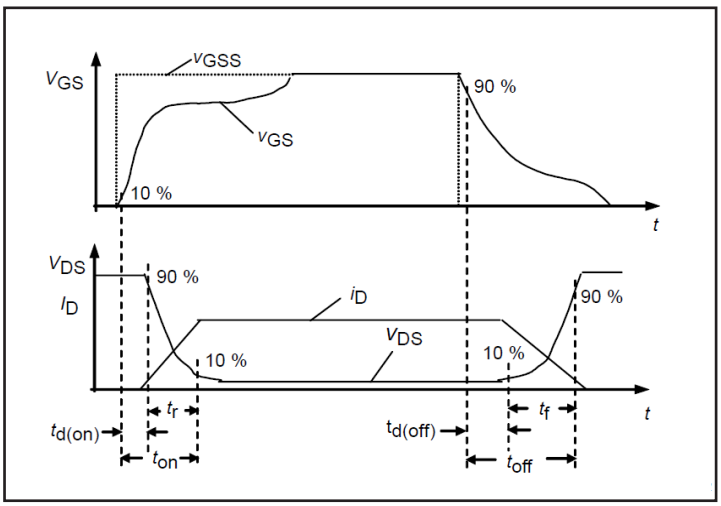


Figure 28. Switching Times Definition

Test Circuit Schematic

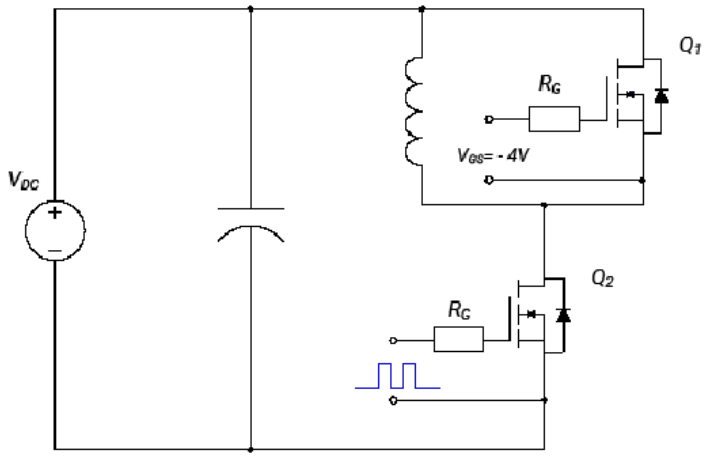
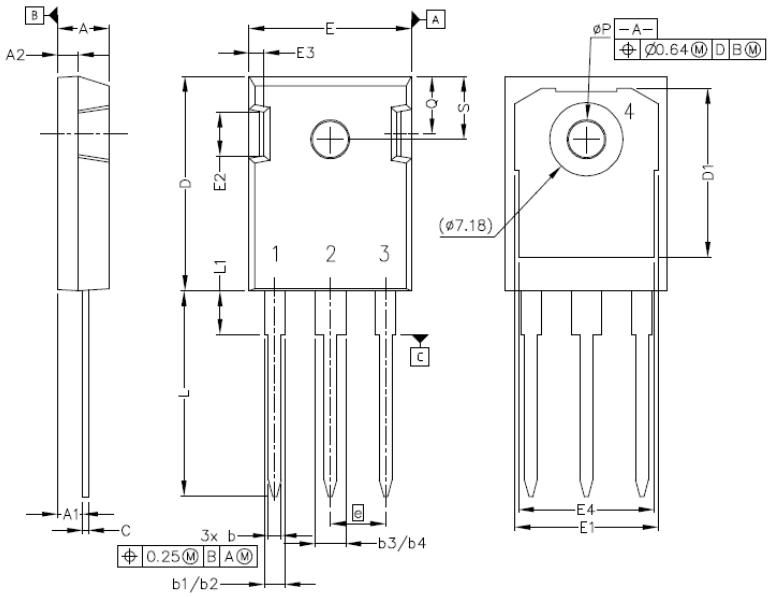


Figure 29. Clamped Inductive Switching
Waveform Test Circuit

Note (3): Turn-off and Turn-on switching energy and timing values measured using SiC MOSFET Body Diode as shown above.

Package Dimensions

Package TO-247-3

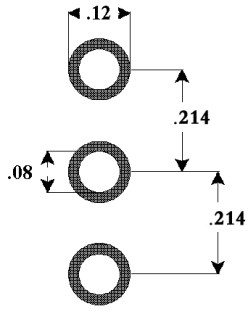


Pinout Information:

- Pin 1 = Gate
- Pin 2, 4 = Drain
- Pin 3 = Source

POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.042	.052	1.07	1.33
b1	.075	.095	1.91	2.41
b2	.075	.085	1.91	2.16
b3	.113	.133	2.87	3.38
b4	.113	.123	2.87	3.13
c	.022	.027	0.55	0.68
D	.819	.831	20.80	21.10
D1	.640	.695	16.25	17.65
D2	.037	.049	0.95	1.25
E	.620	.635	15.75	16.13
E1	.516	.557	13.10	14.15
E2	.145	.201	3.68	5.10
E3	.039	.075	1.00	1.90
E4	.487	.529	12.38	13.43
e	.214 BSC		5.44 BSC	
N	3		3	
L	.780	.800	19.81	20.32
L1	.161	.173	4.10	4.40
ØP	.138	.144	3.51	3.65
Q	.216	.236	5.49	6.00
S	.238	.248	6.04	6.30
T	9°	11°	9°	11°
U	9°	11°	9°	11°
V	2°	8°	2°	8°
W	2°	8°	2°	8°

Recommended Solder Pad Layout



TO-247-3

Notes

- **RoHS Compliance**
  The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Cree representative or from the Product Documentation sections of www.cree.com.

- **REACh Compliance**
  REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future,please contact a Cree representative to insure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

- This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, air traffic control systems.

Related Links

- **SPICE Models: http://wolfspeed.com/power/tools-and-support**
- **SiC MOSFET Isolated Gate Driver reference design: http://wolfspeed.com/power/tools-and-support**
- **SiC MOSFET Evaluation Board: http://wolfspeed.com/power/tools-and-support**

Cree, Inc.
4600 Silicon Drive
Durham, NC 27703
USA Tel: +1.919.313.5300
Fax: +1.919.313.5451
www.wolfspeed.com/power